

# Luis Scalvi

## List of Publications by Year in descending order

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98  
papers

1,083  
citations

394286

19  
h-index

526166

27  
g-index

102  
all docs

102  
docs citations

102  
times ranked

941  
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of Pb <sup>2+</sup> doping in the optical and electro-optical properties of SnO <sub>2</sub> thin films. <i>Materials Chemistry and Physics</i> , 2022, 278, 125571.	2.0	6
2	Deposition of hybrid structures of reduced graphene oxide and tin dioxide thin films, and persistent photoconductivity observation. <i>Current Applied Physics</i> , 2022, 41, 49-58.	1.1	2
3	Zirconium oxide film deposition properties to build transparent electronic devices in conjunction with tin dioxide. <i>International Journal of Modern Physics B</i> , 2022, 36, .	1.0	2
4	Synthesis and Characterization of Cu <sub>2</sub> -xS structures by Different Chemical Routes for Electronic Applications. <i>Materials Research</i> , 2021, 24, .	0.6	1
5	Enhancement of surface properties of sol gel tin dioxide thin films with addition of surfactant in the precursor solution. <i>Applied Physics A: Materials Science and Processing</i> , 2021, 127, 1.	1.1	4
6	Anomalous diode behavior of Cu <sub>2</sub> S/SnO <sub>2</sub> p-n junction. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 21804-21812.	1.1	2
7	Deposition of TiO <sub>2</sub> thin Films by Dip-Coating Technique from a Two-Phase Solution Method and Application to Photocatalysis. <i>Materials Research</i> , 2021, 24, .	0.6	7
8	Transient decay of photoinduced current in semiconductors and heterostructures. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 033001.	1.3	12
9	Low-temperature ZrO <sub>2</sub> thin films obtained by polymeric route for electronic applications. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 16065-16072.	1.1	3
10	A dynamic time-temperature-dependent process for thermal oxidation of Sn leading to SnO <sub>x</sub> thin films: Impedance spectroscopy study. <i>International Journal of Modern Physics B</i> , 2020, 34, 2050184.	1.0	1
11	Photo-induced electrical behavior under gas adsorption on SnO <sub>2</sub> -based heterostructures. <i>Materials Chemistry and Physics</i> , 2020, 255, 123510.	2.0	0
12	Anatase-Rutile Transition and Photo-Induced Conductivity of Highly Yb-Doped TiO <sub>2</sub> Films Deposited by Acid Sol-Gel Dip-Coating Method. <i>Journal of Electronic Materials</i> , 2020, 49, 6369-6379.	1.0	1
13	X-ray absorption spectroscopy and Eu <sup>3+</sup> -emission characteristics in GaAs/SnO <sub>2</sub> heterostructure. <i>SN Applied Sciences</i> , 2020, 2, 1.	1.5	5
14	Influence of thermal annealing on the properties of evaporated Er-doped SnO <sub>2</sub> . <i>Materials Research Bulletin</i> , 2019, 120, 110585.	2.7	8
15	Generation and Propagation of Superhigh-Frequency Bulk Acoustic Waves in GaAs. <i>Physical Review Applied</i> , 2019, 12, .	1.5	11
16	Influence of substrate temperature on the deposition of the homostructure SnO <sub>2</sub> :Sb/SnO <sub>2</sub> :Er via sol-gel dip-coating. <i>Ferroelectrics</i> , 2019, 545, 10-21.	0.3	1
17	Annealing temperature influence on sol-gel processed zirconium oxide thin films for electronic applications. <i>Ceramics International</i> , 2018, 44, 10790-10796.	2.3	20
18	Investigation of sensing properties of sol-gel processed 4Åt%Sb:SnO <sub>2</sub> /TiO <sub>2</sub> thin films. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 467-473.	1.1	4

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19	Thermal Annealing Influence on the Properties of Heterostructure Based on 2Åat.%Eu Doped SnO <sub>2</sub> and Cu <sub>1.8</sub> S. <i>Journal of Electronic Materials</i> , 2018, 47, 7463-7471.	1.0	4
20	Ambipolar transport in tin dioxide thin film transistors promoted by PCBM fullerene. <i>Journal of Materials Science: Materials in Electronics</i> , 2018, 29, 20010-20016.	1.1	6
21	On the photo-induced electrical conduction related to gas sensing of the Sb:SnO <sub>2</sub> /TiO <sub>2</sub> heterostructure. <i>Sensors and Actuators A: Physical</i> , 2018, 281, 250-257.	2.0	8
22	Electron trapping in the photo-induced conductivity decay in GaAs/SnO <sub>2</sub> heterostructure. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	1.1	5
23	Memristive behavior of the SnO <sub>2</sub> /TiO <sub>2</sub> interface deposited by sol-gel. <i>Applied Surface Science</i> , 2017, 410, 278-281.	3.1	29
24	Interface conduction and photo-induced electrical transport in the heterojunction formed by GaAs and Ce <sup>3+</sup> -doped SnO <sub>2</sub> . <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 5415-5424.	1.1	3
25	Photoluminescence of Rare-Earth Ions in the Nanocrystalline GaAs/SnO <sub>2</sub> Heterostructure and the Photoinduced Electrical Properties Related to the Interface. <i>Condensed Matter</i> , 2017, 2, 9.	0.8	3
26	Emission Properties Related to Distinct Phases of Sol-Gel Dip-Coating Titanium Dioxide, and Carrier Photo-Excitation in Different Energy Ranges. <i>Materials Research</i> , 2017, 20, 866-873.	0.6	11
27	Effects of Solution History on Sol-Gel Processed Tin-Oxide Thin-Film Transistors. <i>Journal of the American Ceramic Society</i> , 2016, 99, 4000-4006.	1.9	6
28	On the electrical properties of distinct Eu <sup>3+</sup> emission centers in the heterojunction GaAs/SnO <sub>2</sub> . <i>Thin Solid Films</i> , 2016, 612, 303-309.	0.8	7
29	Dip-coating deposition of resistive BiVO <sub>4</sub> thin film and evaluation of their photoelectrochemical parameters under distinct sources illumination. <i>Journal of Solid State Electrochemistry</i> , 2016, 20, 1527-1538.	1.2	4
30	Improved electrical transport in lightly Er-doped sol-gel spin-coating SnO <sub>2</sub> thin films, processed by photolithography. <i>Applied Physics A: Materials Science and Processing</i> , 2015, 118, 1419-1427.	1.1	11
31	Photoelectrochemical properties of FTO/p-NiO electrode induced by UV light irradiation. <i>Ionics</i> , 2015, 21, 1407-1415.	1.2	4
32	Luminescence of Eu <sup>3+</sup> in the thin film heterojunction GaAs/SnO <sub>2</sub> . <i>Optical Materials Express</i> , 2015, 5, 59.	1.6	7
33	Dip-coating deposition of BiVO <sub>4</sub> /NiO p-n heterojunction thin film and efficiency for methylene blue degradation. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 7705-7714.	1.1	17
34	Heterojunction between Al <sub>2</sub> O <sub>3</sub> and SnO <sub>2</sub> thin films for application in transparent FET. <i>Materials Research</i> , 2014, 17, 1420-1426.	0.6	10
35	A Theoretical Analysis of Sb <sup>5+</sup> Incorporation in Highly Doped SnO <sub>2</sub> Matrix. <i>Current Physical Chemistry</i> , 2014, 4, 15-20.	0.1	0
36	Al <sub>2</sub> O <sub>3</sub> Obtained through Resistive Evaporation for Use as Insulating Layer in Transparent Field Effect Transistor. <i>Advanced Materials Research</i> , 2014, 975, 248-253.	0.3	1

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37	Photoelectrochemical properties of FTO/m-BiVO <sub>4</sub> electrode in different electrolytes solutions under visible light irradiation. <i>Ionics</i> , 2014, 20, 105-113.	1.2	18
38	Deposition of Al <sub>2</sub> O <sub>3</sub> by resistive evaporation and thermal oxidation of Al to be applied as a transparent FET insulating layer. <i>Ceramics International</i> , 2014, 40, 3785-3791.	2.3	16
39	Preparation of TiO <sub>2</sub> /SnO <sub>2</sub> Thin Films by Sol-Gel Method and Periodic B3LYP Simulations. <i>Journal of Physical Chemistry A</i> , 2014, 118, 5857-5865.	1.1	23
40	Deposition and photo-induced electrical resistivity of dip-coated NiO thin films from a precipitation process. <i>Journal of Materials Science: Materials in Electronics</i> , 2013, 24, 1823-1831.	1.1	5
41	Nanoparticle characterization of Er-doped SnO <sub>2</sub> pellets obtained with different pH of colloidal suspension. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	22
42	Decay of photo-induced conductivity in Sb-doped SnO <sub>2</sub> thin films, using monochromatic light of about bandgap energy. <i>Applied Surface Science</i> , 2013, 267, 164-168.	3.1	23
43	Interface formation of nanostructured heterojunction SnO <sub>2</sub> :Eu/GaAs and electronic transport properties. <i>Applied Surface Science</i> , 2013, 267, 200-205.	3.1	15
44	Photo-Induced conductivity of heterojunction GaAs/Rare-Earth doped SnO <sub>2</sub> . <i>Materials Research</i> , 2013, 16, 831-838.	0.6	3
45	Deposition and characterization of BiVO <sub>4</sub> thin films and evaluation as photoanodes for methylene blue degradation. <i>Journal of Solid State Electrochemistry</i> , 2012, 16, 3267-3274.	1.2	20
46	Photo-induced dipole relaxation current in natural Amethyst. <i>Materials Research</i> , 2012, 15, 461-466.	0.6	2
47	A continuously differentiable upwinding scheme for the simulation of fluid flow problems. <i>Applied Mathematics and Computation</i> , 2012, 218, 8614-8633.	1.4	4
48	Characterization of metallic electrical contacts to SnO <sub>2</sub> thin films lightly doped with Eu <sup>3+</sup> ions, and photo-induced resistivity. <i>Materials Chemistry and Physics</i> , 2012, 134, 994-1000.	2.0	3
49	Influence of pH of colloidal suspension on the electrical conductivity of SnO <sub>2</sub> thin films deposited via Sol-Gel-Dip-Coating. <i>Materials Research</i> , 2011, 14, 113-117.	0.6	12
50	Growth of Al <sub>2</sub> O <sub>3</sub> thin film by oxidation of resistively evaporated Al on top of SnO <sub>2</sub> , and electrical properties of the heterojunction SnO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> . <i>Journal of Materials Science</i> , 2011, 46, 6627-6632.	1.7	13
51	Resistividade do filme depositado via sol-gel e estado de oxidação do dopante Ce na matriz SnO <sub>2</sub> . <i>Ceramica</i> , 2011, 57, 225-230.	0.3	0
52	Interface Formation and Electrical Transport in SnO <sub>2</sub> :Eu <sup>3+</sup> /GaAs Heterojunction Deposited by Sol-Gel Dip-Coating and Resistive Evaporation. <i>Journal of Electronic Materials</i> , 2010, 39, 1170-1176.	1.0	15
53	Numerical simulation of the liquid phase in SnO <sub>2</sub> thin film deposition by sol-gel-dip-coating. <i>Journal of Sol-Gel Science and Technology</i> , 2010, 55, 385-393.	1.1	14
54	Raman and photoluminescence of Er <sup>3+</sup> -doped SnO <sub>2</sub> obtained via the sol-gel technique from solutions with distinct pH. <i>Optical Materials</i> , 2010, 33, 66-70.	1.7	9

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55	Evaluation of bulk and surfaces absorption edge energy of sol-gel-dip-coating SnO <sub>2</sub> thin films. Materials Research, 2010, 13, 437-443.	0.6	19
56	Structural Characterization of Nanocrystalline Sb-Doped SnO <sub>2</sub> Xerogels by Multiedge X-ray Absorption Spectroscopy. Journal of Physical Chemistry C, 2010, 114, 19206-19213.	1.5	15
57	Cr <sup>3+</sup> Distribution in Al <sup>1</sup> and Al <sup>2</sup> Sites of Alexandrite (BeAl <sub>2</sub> O <sub>4</sub> : Cr <sup>3+</sup> ) Induced by Annealing, Investigated by Optical Spectroscopy. Energy and Power Engineering, 2010, 02, 18-24.	0.5	11
58	Determinação de diagramas de bandas de energia e da borda de absorção em SnO <sub>2</sub> , depositado via sol-gel, sobre quartzo. Cerâmica, 2009, 55, 88-93.	0.3	1
59	Optical emission and electron capture of rare-earth trivalent ions located at distinct sites in SnO <sub>2</sub> thin films. Physics Procedia, 2009, 2, 353-364.	1.2	8
60	Effect of pH of colloidal suspension on crystallization and activation energy of deep levels in SnO <sub>2</sub> thin films obtained via sol-gel. Journal of Physics and Chemistry of Solids, 2009, 70, 1312-1316.	1.9	17
61	Photoluminescence of Eu <sup>3+</sup> ion in SnO <sub>2</sub> obtained by sol-gel. Journal of Materials Science, 2008, 43, 345-349.	1.7	61
62	Schottky emission in nanoscopically crystallized Ce-doped SnO <sub>2</sub> thin films deposited by sol-gel-dip-coating. Thin Solid Films, 2008, 517, 976-981.	0.8	22
63	Rare earth centers properties and electron trapping in SnO <sub>2</sub> thin films produced by sol-gel route. Journal of Non-Crystalline Solids, 2008, 354, 4840-4845.	1.5	30
64	Powder Diffraction of Components Subject to Corrosion in Fuse Cutouts with Ceramic Insulation. Materials Science Forum, 2008, 591-593, 548-553.	0.3	0
65	Optical excitation of charge carriers from intra-bandgap states in Ce-doped SnO <sub>2</sub> thin films. AIP Conference Proceedings, 2008, . .	0.3	0
66	Visible emission from Er-doped SnO <sub>2</sub> thin films deposited by sol-gel. Cerâmica, 2007, 53, 187-191.	0.3	9
67	Electron trapping of laser-induced carriers in Er-doped SnO <sub>2</sub> thin films. Journal of the European Ceramic Society, 2007, 27, 3803-3806.	2.8	28
68	EXAFS investigation on Sb incorporation effects to electrical transport in SnO <sub>2</sub> thin films deposited by sol-gel. Journal of the European Ceramic Society, 2007, 27, 4265-4268.	2.8	31
69	Decay of photo-excited conductivity of Er-doped SnO <sub>2</sub> thin films. Journal of Materials Science, 2007, 42, 2216-2221.	1.7	18
70	Analysis of Er <sup>3+</sup> incorporation in SnO <sub>2</sub> by optical investigation. Brazilian Journal of Physics, 2006, 36, 270-273.	0.7	8
71	Drude's model calculation rule on electrical transport in Sb-doped SnO <sub>2</sub> thin films, deposited via sol-gel. Journal of Physics and Chemistry of Solids, 2006, 67, 1410-1415.	1.9	49
72	Ultraviolet excitation of photoconductivity in thin films of sol-gel SnO <sub>2</sub> . Journal of the European Ceramic Society, 2005, 25, 2825-2828.	2.8	14

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73	Thermal annealing-induced electric dipole relaxation in natural alexandrite. <i>Physics and Chemistry of Minerals</i> , 2005, 31, 733-737.	0.3	7
74	Poole-Frenkel effect in Er doped SnO <sub>2</sub> thin films deposited by sol-gel-dip-coating. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 301-308.	0.8	31
75	Photoconductivity excitation spectrum for stretch-oriented PPV. <i>Synthetic Metals</i> , 2005, 154, 77-80.	2.1	2
76	Electro-optical properties of Er-doped SnO <sub>2</sub> thin films. <i>Journal of the European Ceramic Society</i> , 2004, 24, 1857-1860.	2.8	38
77	Annealing effects on optical properties of natural alexandrite. <i>Journal of Physics Condensed Matter</i> , 2003, 15, 7437-7443.	0.7	12
78	Sb doping effects and oxygen adsorption in SnO <sub>2</sub> thin films deposited via sol-gel. <i>Materials Research</i> , 2003, 6, 451-456.	0.6	38
79	Er rare-earth ion incorporation in sol-gel SnO <sub>2</sub> . <i>Materials Research</i> , 2003, 6, 445-449.	0.6	8
80	Planar Waveguides Based on Nanocrystalline and Er <sup>3+</sup> Doped SnO <sub>2</sub> . <i>Journal of Metastable and Nanocrystalline Materials</i> , 2002, 14, 107-110.	0.1	4
81	Planar Waveguides Based on Nanocrystalline and Er <sup>3+</sup> Doped SnO <sub>2</sub> . <i>Materials Science Forum</i> , 2002, 403, 107-110.	0.3	1
82	Optical characteristics of Er <sup>3+</sup> Yb <sup>3+</sup> doped SnO <sub>2</sub> xerogels. <i>Journal of Alloys and Compounds</i> , 2002, 344, 217-220.	2.8	54
83	Light-induced electric dipole relaxation in synthetic and natural alexandrite. <i>Radiation Effects and Defects in Solids</i> , 2001, 156, 295-299.	0.4	4
84	Contribution of oxygen related defects to the electronic transport in SnO <sub>2</sub> sol-gel films. <i>Radiation Effects and Defects in Solids</i> , 2001, 156, 145-149.	0.4	1
85	Photo-induced electron trapping in indirect bandgap at low temperature. <i>Journal of Physics Condensed Matter</i> , 1999, 11, 425-433.	0.7	2
86	Oxygen related defects excitation and photoconductivity dependence of SnO <sub>2</sub> Sol-Gel films with several light sources. <i>Radiation Effects and Defects in Solids</i> , 1999, 150, 391-395.	0.4	3
87	Electron scattering and effects of sources of light on photoconductivity of SnO <sub>2</sub> coatings prepared by sol-gel. <i>Journal of Non-Crystalline Solids</i> , 1999, 247, 171-175.	1.5	30
88	Title is missing!. <i>Journal of Sol-Gel Science and Technology</i> , 1998, 13, 793-798.	1.1	23
89	Photodesorption and electron trapping in n-type SnO <sub>2</sub> thin films grown by dip-coating technique. <i>Radiation Effects and Defects in Solids</i> , 1998, 146, 199-206.	0.4	4
90	Investigation of temperature influence on photo-induced conductivity in n-type Al <sub>x</sub> Ga <sub>1-x</sub> As. <i>Radiation Effects and Defects in Solids</i> , 1998, 146, 175-186.	0.4	1

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91	Light-induced relaxing dipoles in n-type Al <sub>x</sub> Ga <sub>1-x</sub> As. Physical Review B, 1995, 51, 13864-13867.	1.1	4
92	Subband mixing inducing negative resistance. Solid State Communications, 1993, 86, 301-304.	0.9	0
93	Dipole relaxation current in n-type Al <sub>x</sub> Ga <sub>1-x</sub> As. Applied Physics Letters, 1993, 63, 2658-2660.	1.5	3
94	Substitutional donor related states and Au/Ge/Ni contacts to Al <sub>x</sub> Ga <sub>1-x</sub> As. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1993, 68, 727-735.	0.6	1
95	Dipole Relaxation Current in N-Type Al <sub>x</sub> Ga <sub>1-x</sub> As. Materials Research Society Symposia Proceedings, 1993, 325, 285.	0.1	1
96	Transient decay of persistent photoconductivity in Al <sub>0.3</sub> Ga <sub>0.7</sub> As. Journal of Applied Physics, 1990, 68, 601-605.	1.1	23
97	Nanostructured TiO <sub>2</sub> -Based Composites for Light Absorption. Advanced Materials Research, 0, 975, 207-212.	0.3	0
98	Investigation of Photoinduced Electrical Properties in the Heterojunction TiO <sub>2</sub> /SnO <sub>2</sub> . Advanced Materials Research, 0, 975, 201-206.	0.3	0